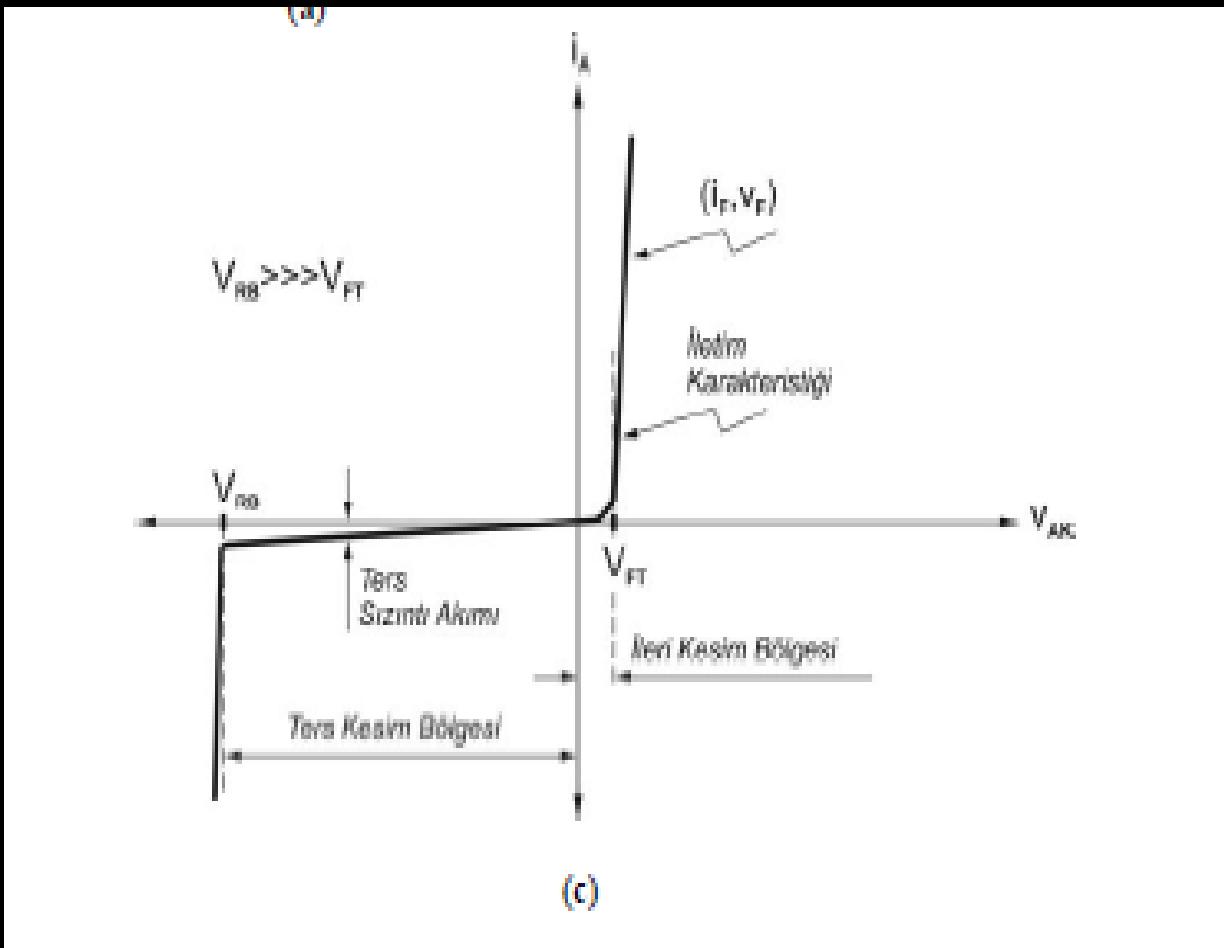
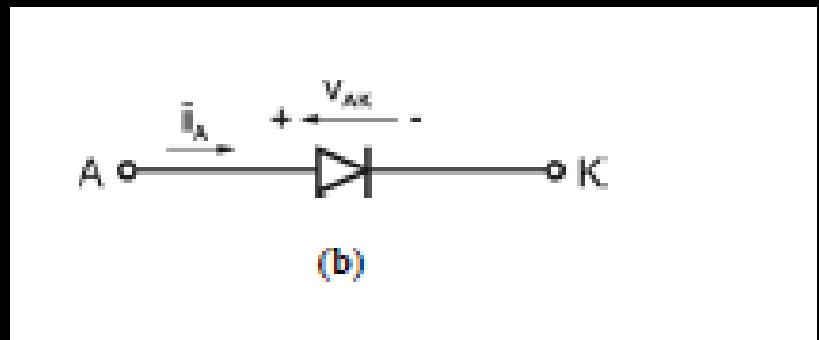
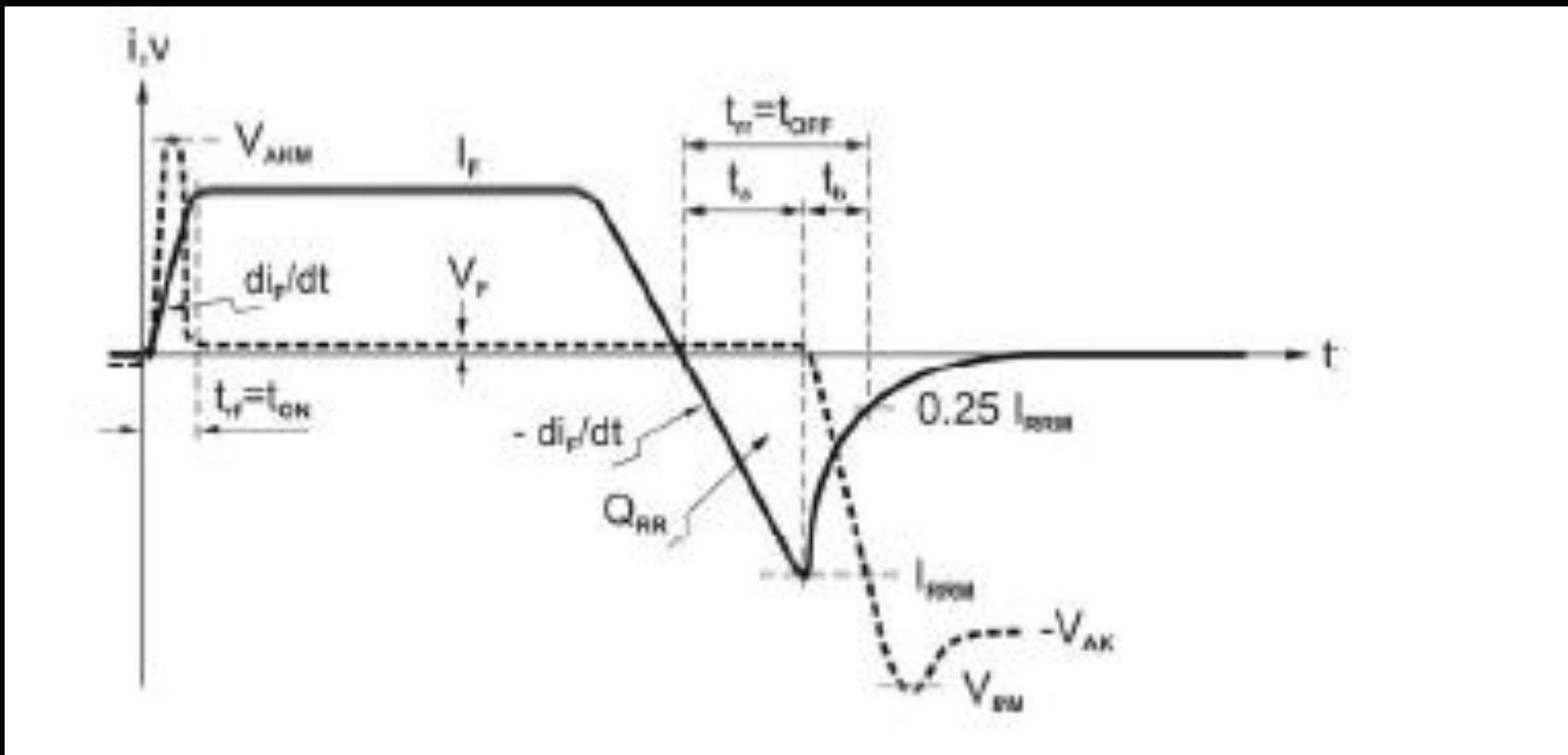

POWER ELECTRONIC 2

2020, Istanbul

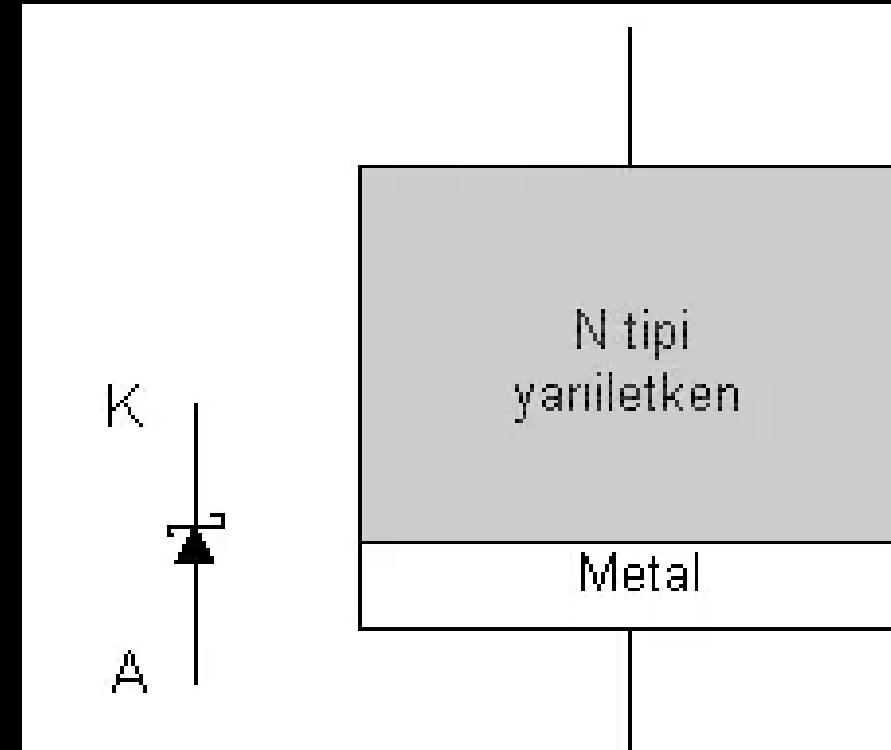
Power Diodes



Power Diodes

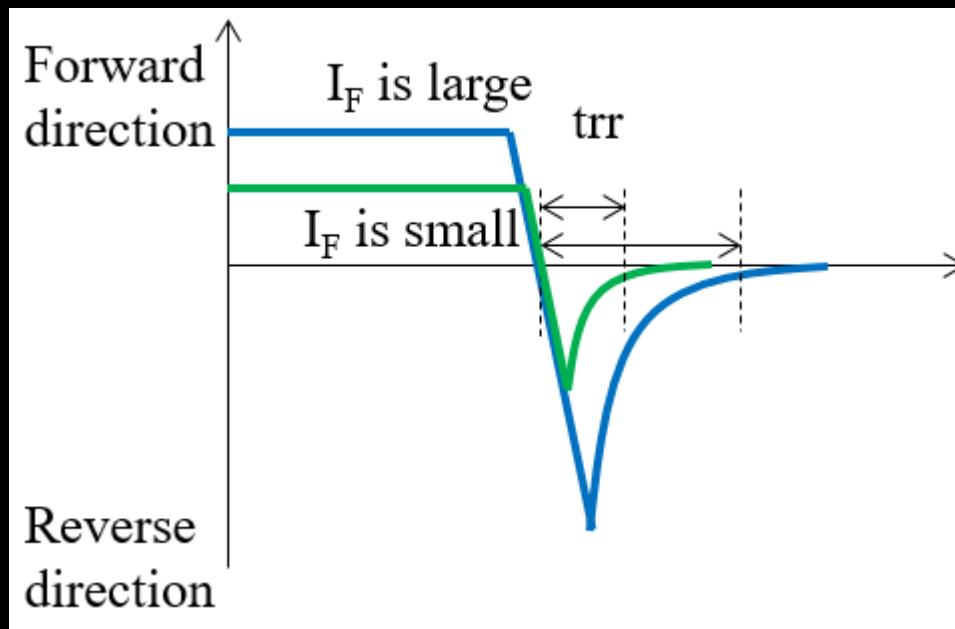
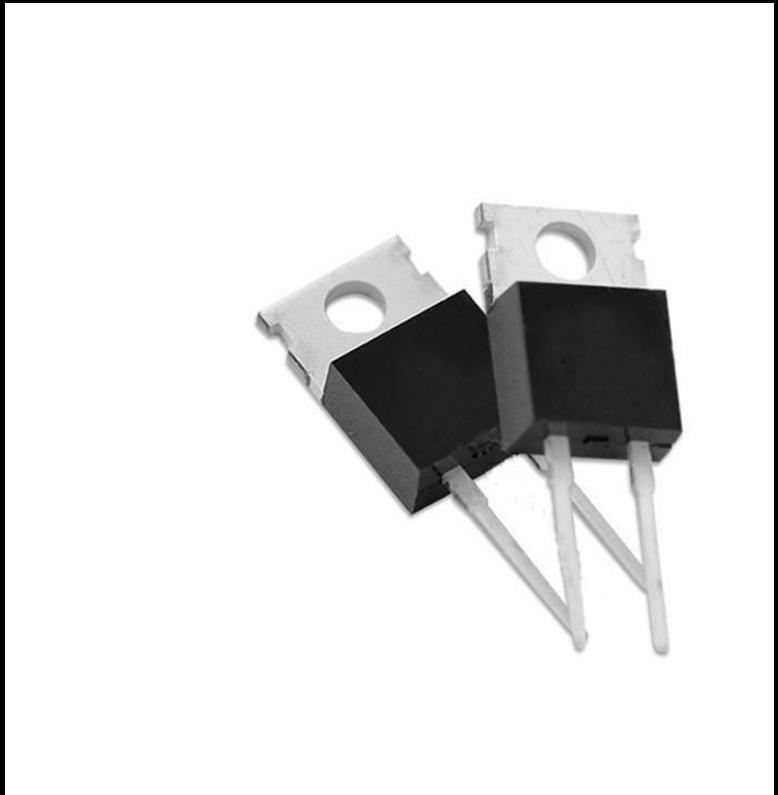


Diode Types



Schottky Diode

Silisyum-metal birleşimi



Fast Recovery Diode

Thyristors

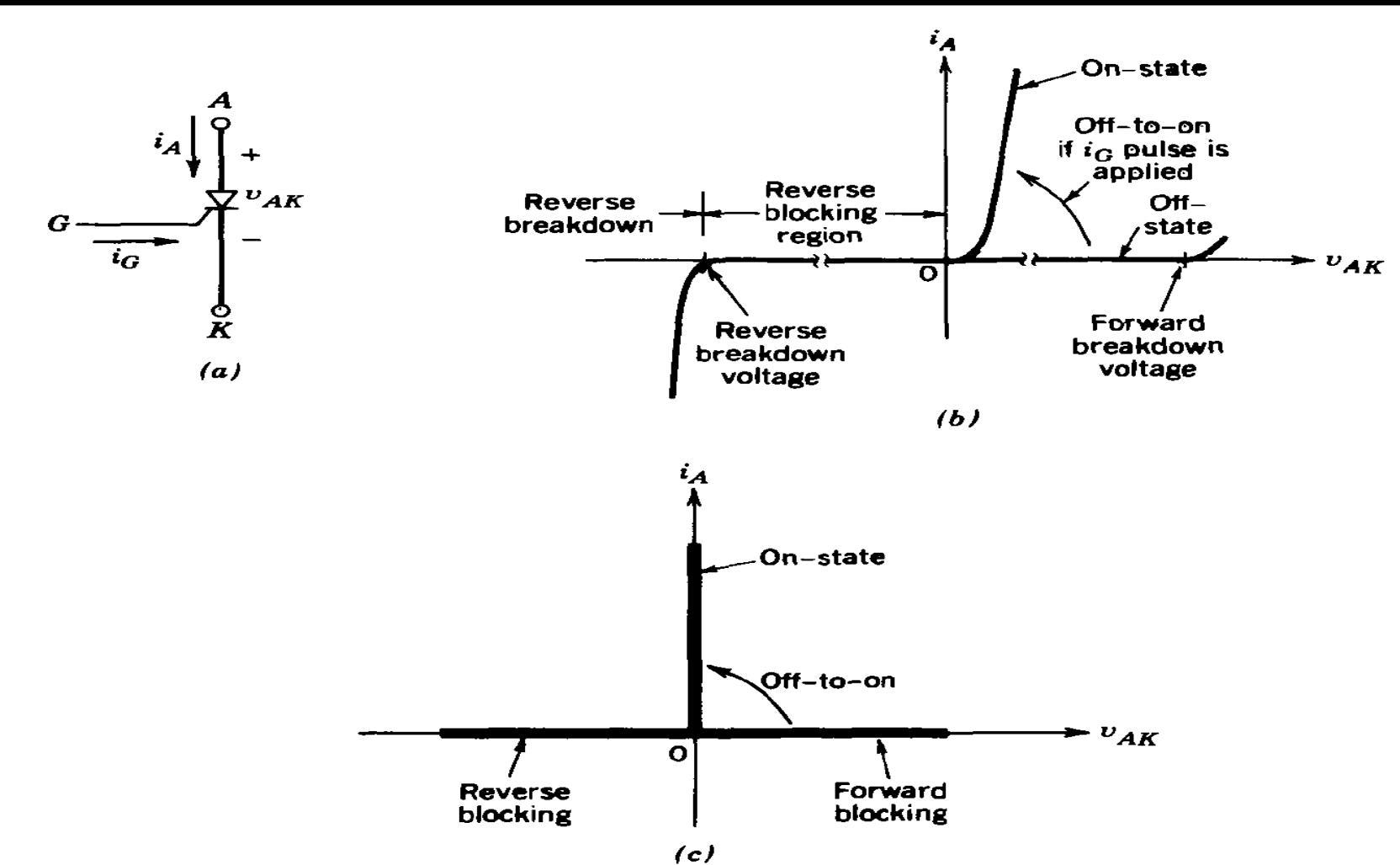
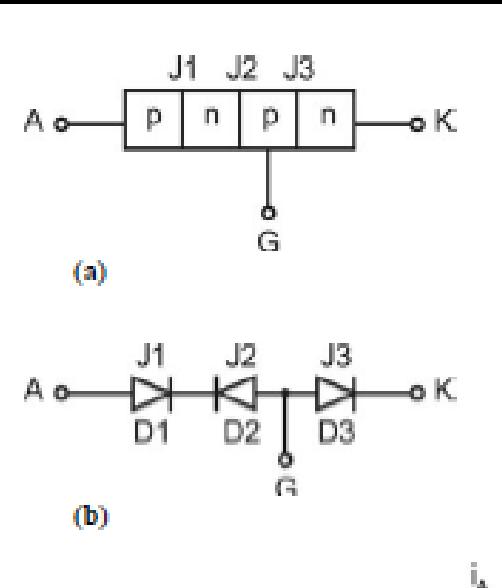
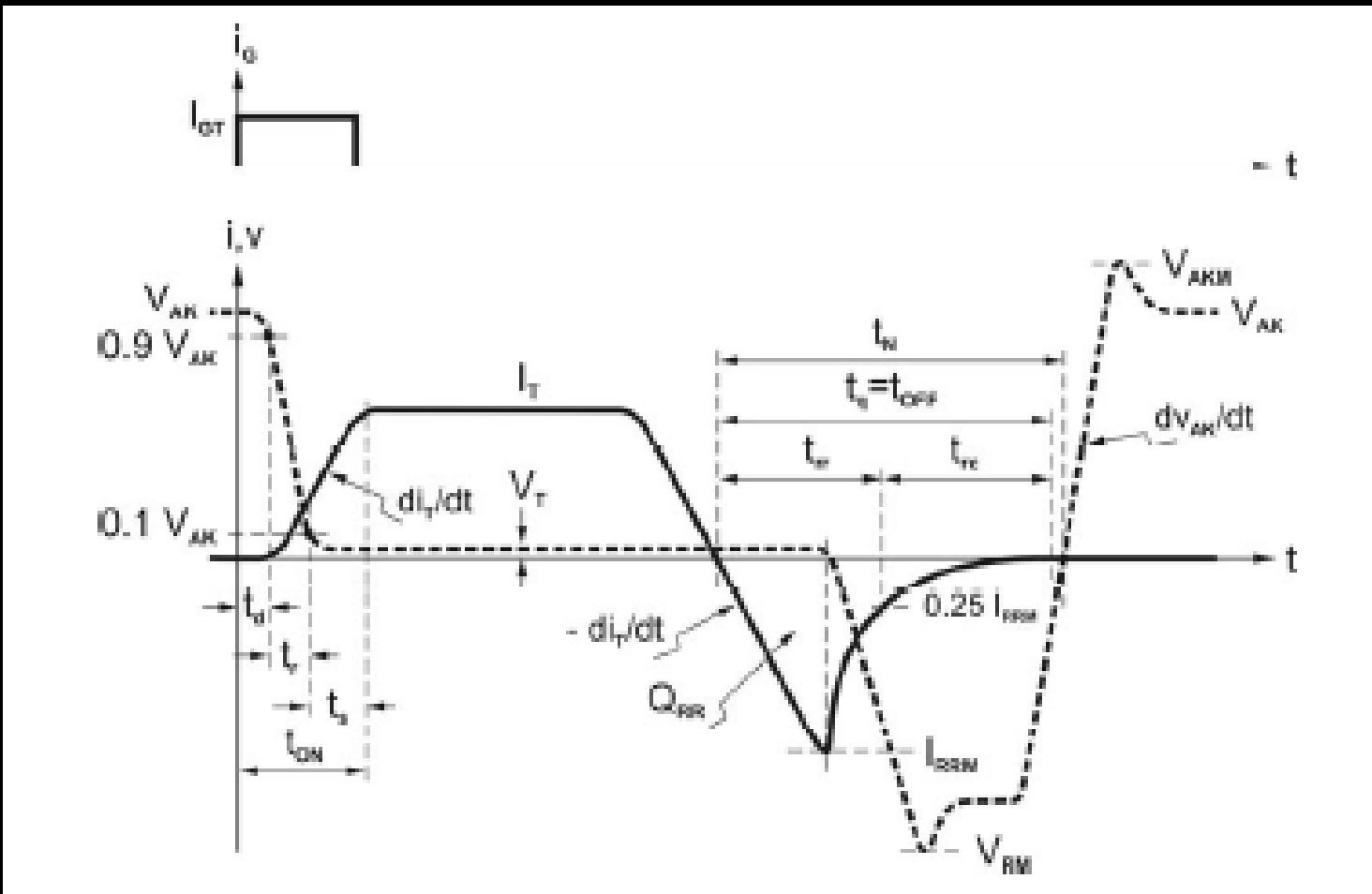
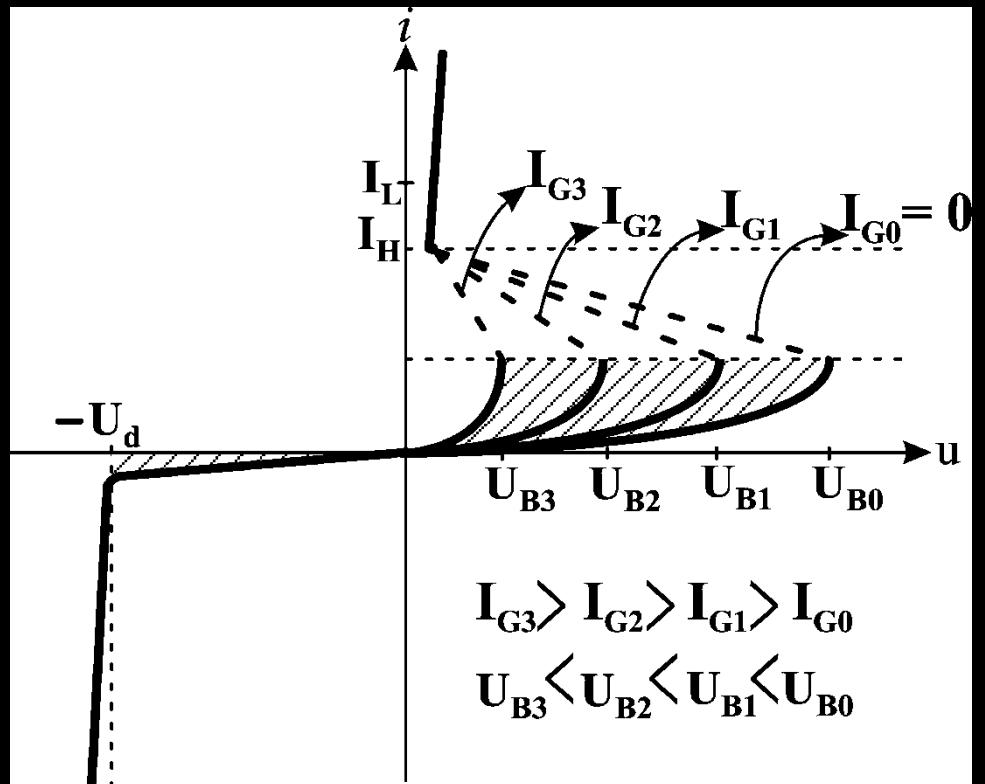
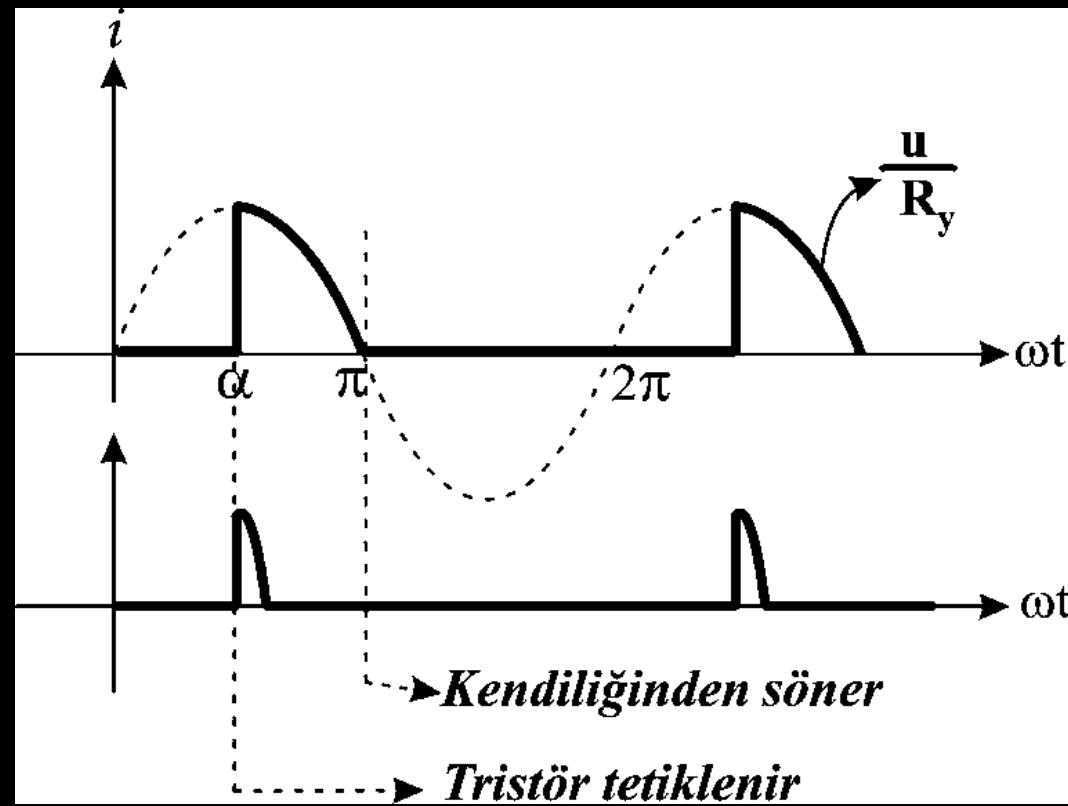
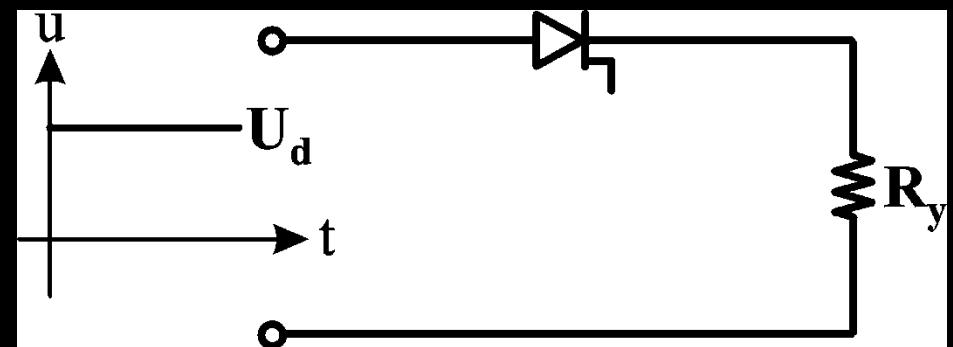
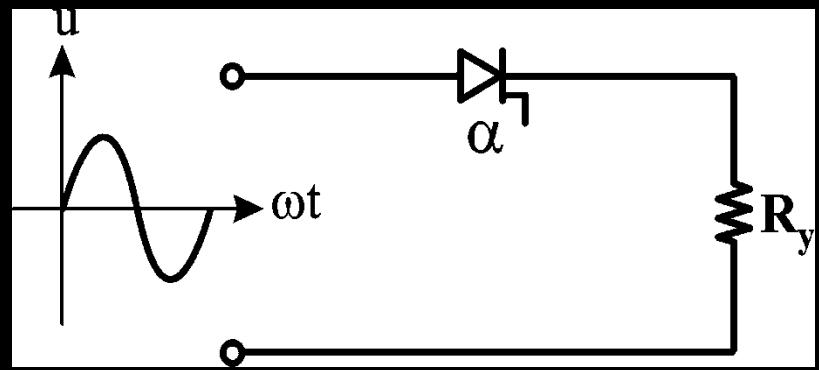


Figure 2-3 Thyristor: (a) symbol, (b) $i-v$ characteristics, (c) idealized characteristics.

Thyristors



Thyristors



The Bipolar Junction Transistor (BJT)

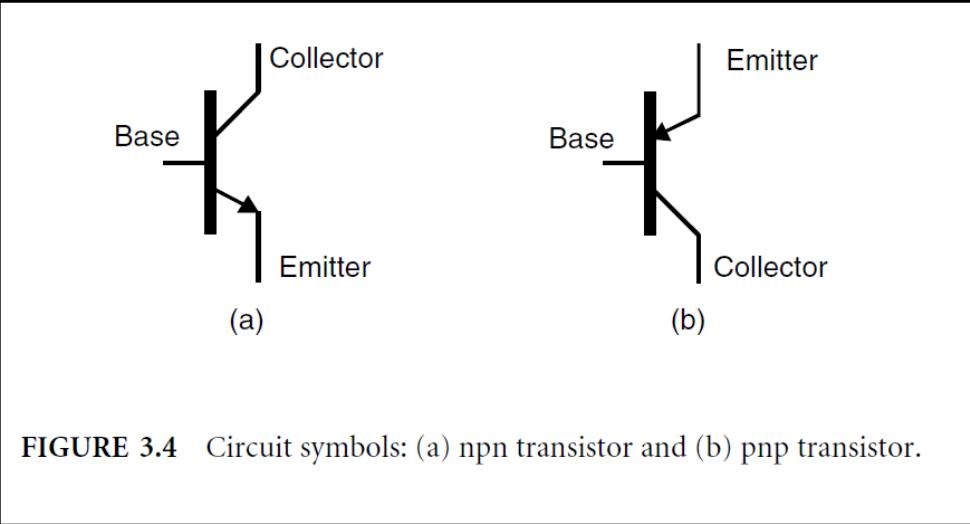
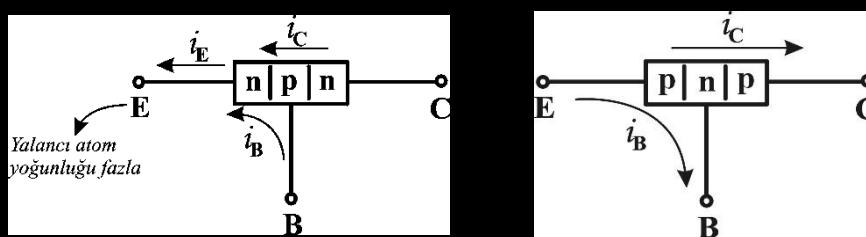


FIGURE 3.4 Circuit symbols: (a) npn transistor and (b) pnp transistor.



The Bipolar Junction Transistor (BJT)

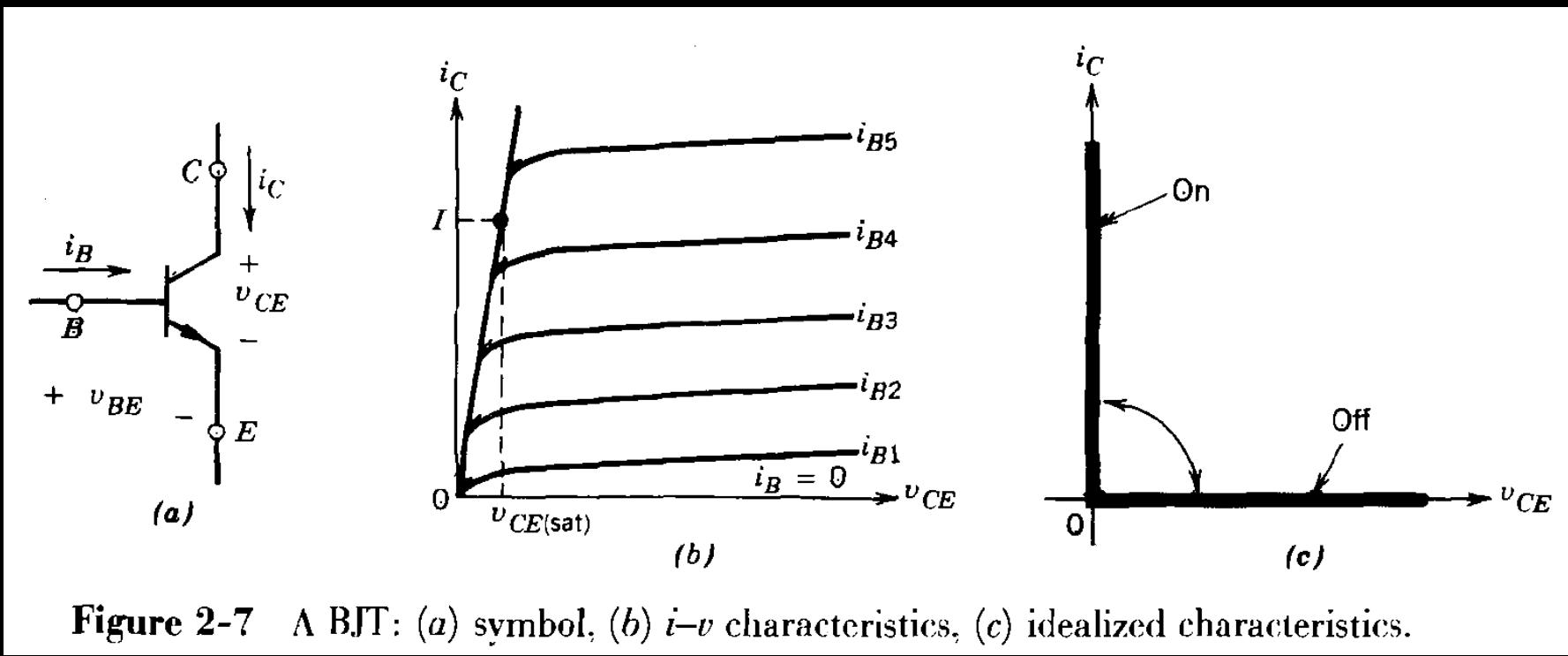
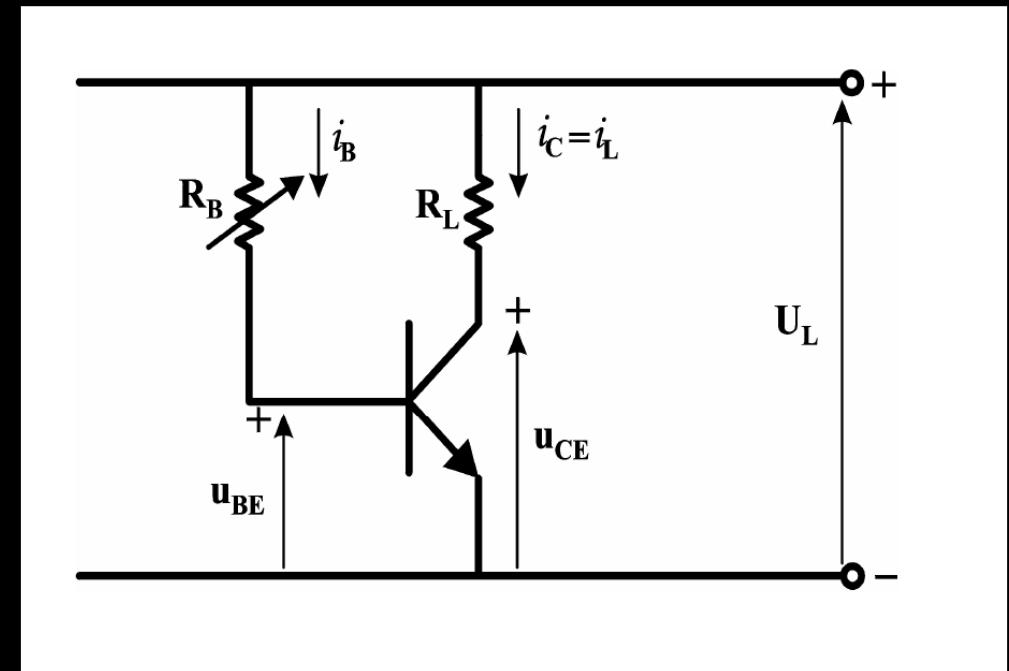
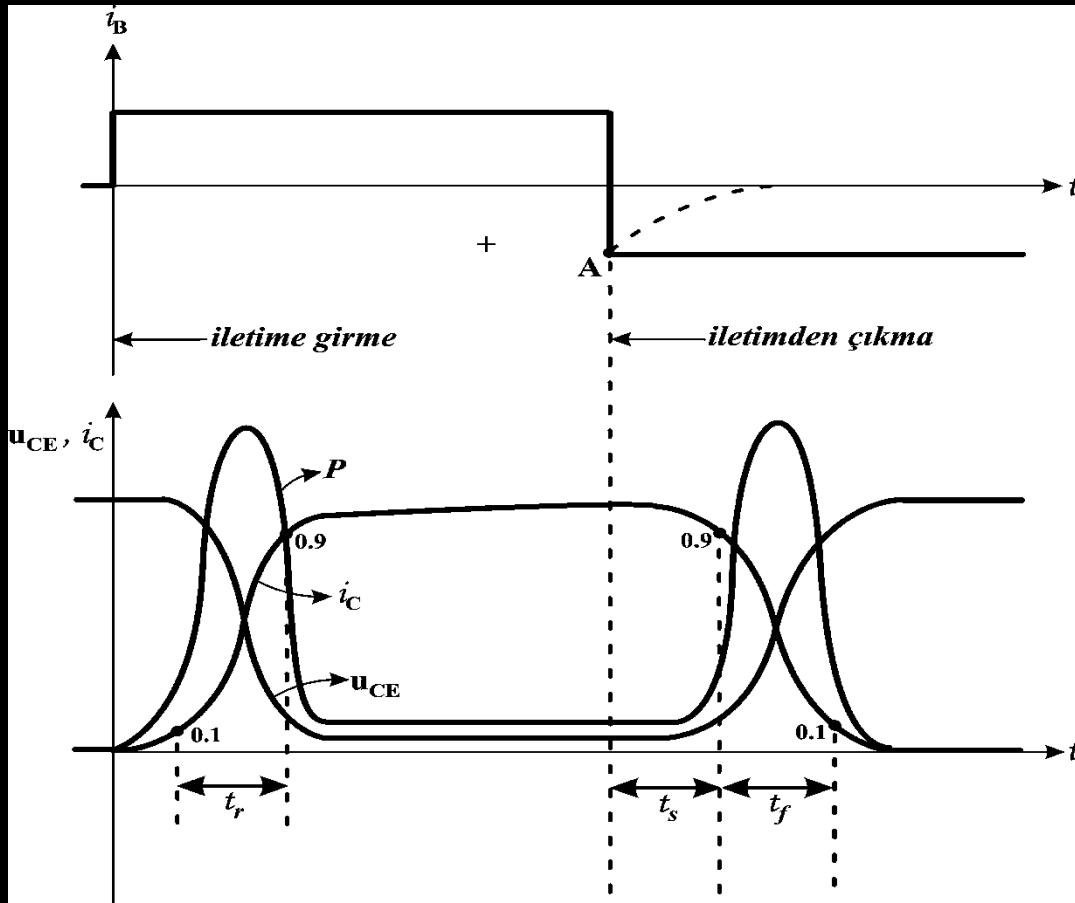
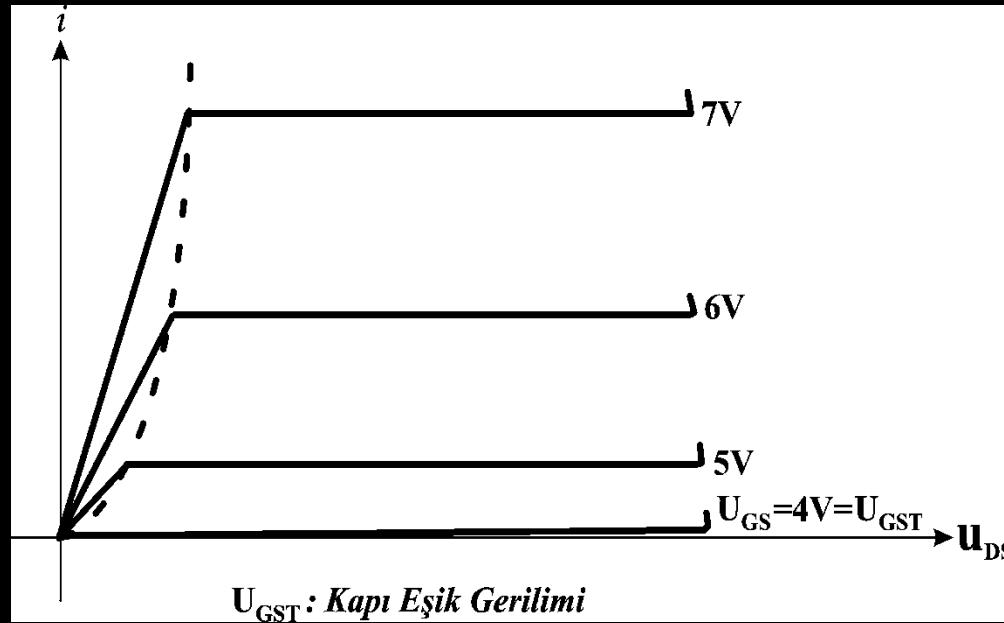
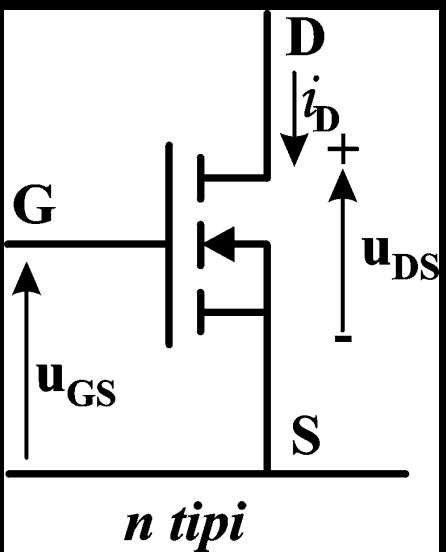


Figure 2-7 A BJT: (a) symbol, (b) i - v characteristics, (c) idealized characteristics.

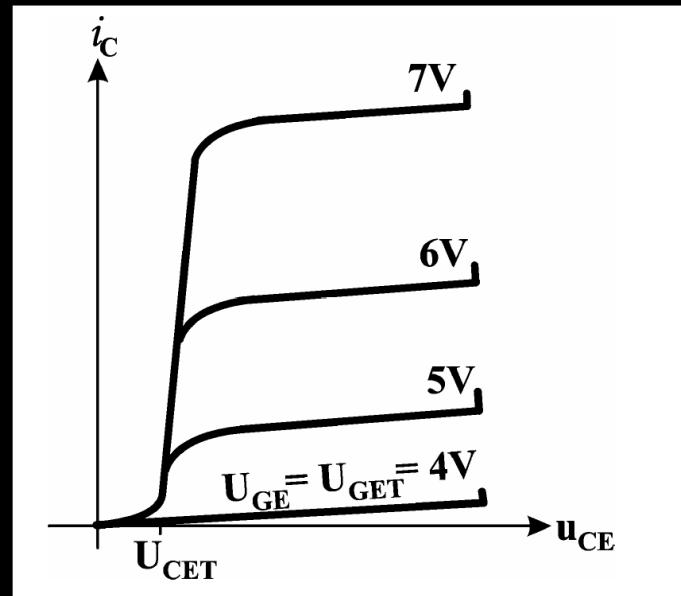
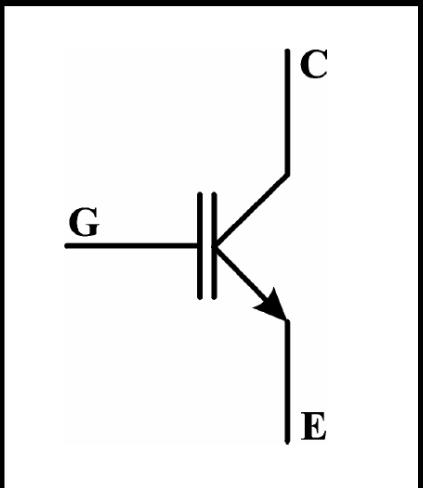
The Bipolar Junction Transistor (BJT)

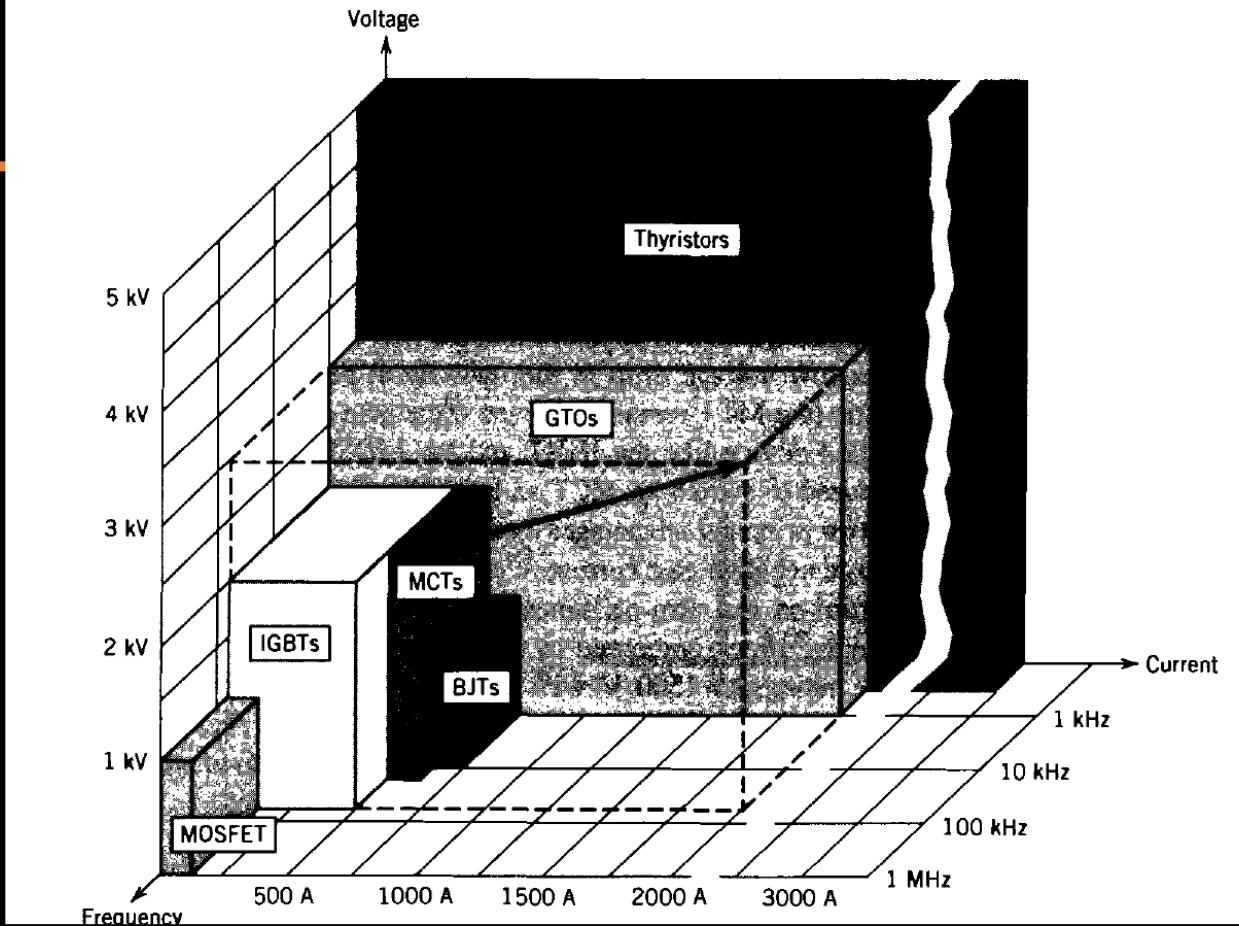


(MOSFET)



(IGBT)





<i>Device</i>	<i>Power Capability</i>	<i>Switching Speed</i>
BJT/MD	Medium	Medium
MOSFET	Low	Fast
GTO	High	Slow
IGBT	Medium	Medium
MCT	Medium	Medium